Supporting Materials for "Pressure induced superconductivity bordering a charge-density-wave state in $NbTe_4$ with strong spin-orbit coupling"

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The field dependences of ρ_{xx} and ρ_{yx} are fit by the following equations:

$$\rho_{xx}(B) = \frac{1}{e}\frac{(n_h\mu_h + n_e\mu_e) + (n_h\mu_e + n_e\mu_h)\mu_h\mu_e B^2}{(n_h\mu_h + n_e\mu_e)^2 + (n_h - n_e)^2\mu_h^2\mu_e^2 B^2} \tag{1}$$

$$\rho_{yx}(B) = \frac{B}{e}\frac{(n_h\mu_h^2 - n_e\mu_e^2) + (n_h - n_e)\mu_h^2\mu_e^2 B^2}{(n_h\mu_h + n_e\mu_e)^2 + (n_h - n_e)^2\mu_h^2\mu_e^2 B^2} \tag{2}$$

where n_e, n_h, μ_e and μ_h are the carrier densities and mobilities of electrons and holes, respectively. Simultaneously fitting our ambient pressure data with the above equations in the low field region ($B \leq 1$ T), we can get the temperature dependences of n_e, n_h, μ_e and μ_h. The fitted curves are displayed as lines in Fig. S1(a) and S1(b) and they agree well with the experimental data in the field region of 0 T - 1 T.

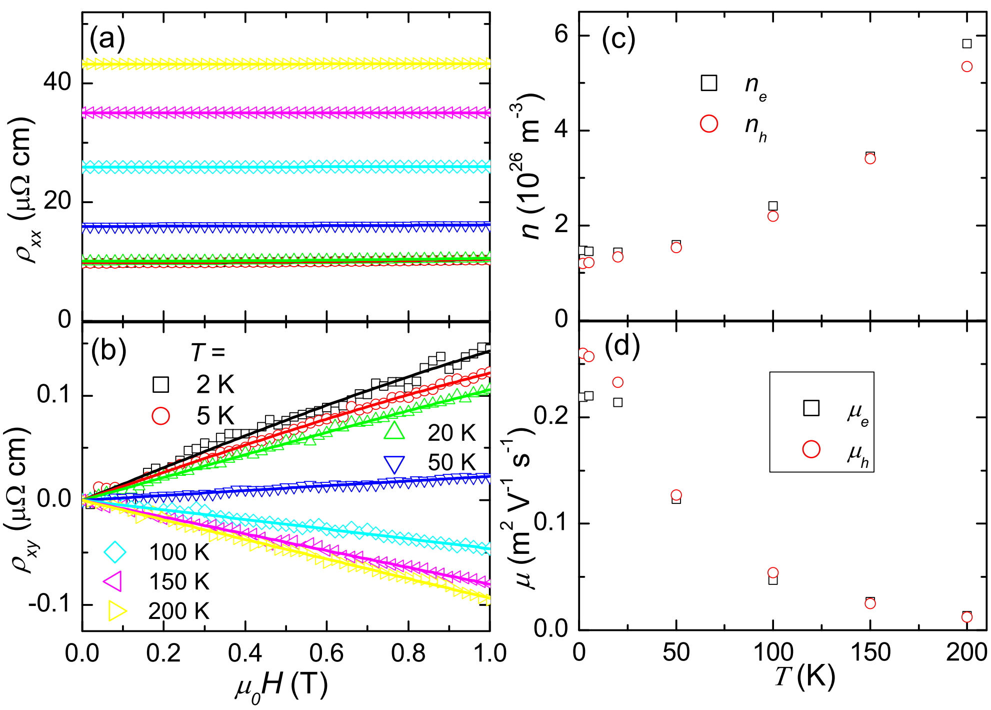

FIG. S 1: **Two band model fitting of low field transport properties of $NbTe_4$ single crystal with I//c-axis and B//b-axis.** Field dependence of **(a)**, transverse magnetoresistivity ρ_{xx} and **(b)**, Hall resistivity ρ_{yx}. The symbols correspond to experimental data, while the lines are the fitting curves by the two-band model. **(c)** and **(d)** display the temperature dependence of carrier density and mobility, respectively.